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PATENT  
Attorney Docket No.: SAM-0298

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant(s): Jae-Hak Kim, et al. Examiner: Rao, S.  
Serial No.: 09/994,508 Group Art Unit: 2814  
Filing Date: November 27, 2001  
Title: METHOD OF FABRICATING SEMICONDUCTOR DEVICES HAVING LOW  
DIELECTRIC INTERLAYER INSULATION LAYER

CERTIFICATE OF MAILING UNDER 37 C.F.R. § 1.8

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6-20-02  
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Amy Green  
Amy Green

BOX NON-FEE AMENDMENT  
Assistant Commissioner for Patents  
Washington, D.C. 20231

AMENDMENT A

Sir:

This is in response to the Office Action mailed on March 20, 2002.

Please amend the application as follows:

In the Claims

- ~~1. (Amended) A method of fabricating a semiconductor device having a low dielectric interlayer insulation layer, the method comprising:~~
- ~~forming a silicon oxycarbide layer as the low dielectric interlayer insulation layer on a substrate;~~
  - ~~after the silicon oxycarbide layer is formed, treating the silicon oxycarbide layer with plasma; and~~
  - ~~stacking photoresist on the plasma-treated oxycarbide layer and patterning the resultant structure.~~

Sub B

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